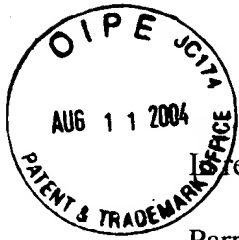


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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Re Application of :
Parris C.M. HAWKINS et al. :
Serial No. 09/800,980 : Group Art Unit: 2125
Filed: March 8, 2001 : Examiner: Sean P. Shechtman
For: DYNAMIC AND EXTENSIBLE TASK GUIDE

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Honorable Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

In accordance with the provisions of 37 C.F.R. 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the documents listed on the attached form PTO-1449. It is respectfully requested that the documents be expressly considered during the prosecution of this application, and that the documents be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This submission does not constitute a representation that a search has been made or that no better art exists and does not constitute an admission or representation that any of the listed documents is material or constitutes prior art. If it should be determined that any of the listed documents does not constitute prior art under the United States law, Applicants reserve the right

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Serial No. 09/800,980

to present to the Office the relevant facts and law regarding the appropriate status of such document.

Please charge the fee of \$180.00 under 37 CFR 1.17(p) to Deposit Account No. 08-0219. The Commissioner is authorized to charge any deficiency in any fees pursuant to 37 CFR § 1.17 associated with this communication and to credit any excess payment to Deposit Account No. 08-0219.

Respectfully submitted,

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				APPLICANT Parris C.M. HAWKINS et al.			
				FILING DATE March 8, 2001		GROUP 2125	
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